



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

2SC2073 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1.5 A

Collector-base voltage

$V_{(BR)CBO}$: 150 V

Operating and storage junction temperature range

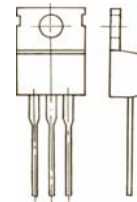
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-220

1. BASE

2. COLLECTOR

3. EMITTER



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ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=120V, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=500mA$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=10V, I_C=500mA$	0.65		0.85	V
Transition frequency	f_T	$V_{CE}=10V, I_C=500mA$		4		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		35		pF